

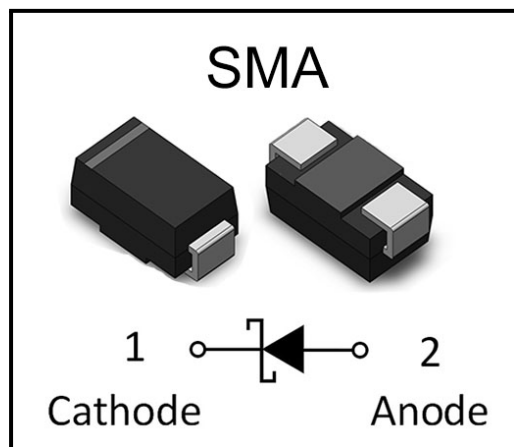
SS12-SS120

Schottky Barrier Diode

Features

- For surface mounted applications
- Metal silicon junction, majority carrier conduction
- Low power loss, high efficiency
- Built-in strain relief, ideal for automated placement
- High forward surge current capability
- High temperature soldering guaranteed:
250°C/10 seconds at terminals

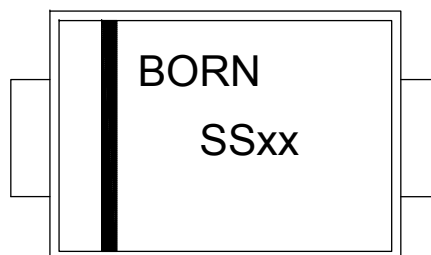
Package



Description

- Case: JEDEC DO-214AC molded plastic
- Terminals: Axial leads. Solderable per MIL-STD-750 Method 2026
- Polarity: Color band denotes cathode
- Mounting Position: Any

Marking



Ordering information

Part Number	SS12	SS13	SS14	SS15	SS16	SS18	SS110	SS115	SS120
Marking	SS12	SS13	SS14	SS15	SS16	SS18	SS110	SS115	SS120
Base qty	5K	5K	5K	5K	5K	5K	5K	5K	5K



SS12-SS120

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Maximum Ratings and Electrical Characteristics@T_A=25°C unless otherwise noted

Symbol	Parameters	SS 12	SS 13	SS 14	SS 15	SS 16	SS 18	SS 110	SS 115	SS 120	Units
V _{RRM}	Maximum Recurrent Peak Reverse Voltage	20	30	40	50	60	80	100	150	200	V
V _{RMS}	Maximum RMS Voltage	14	21	28	35	42	56	70	105	140	V
V _{DC}	Maximum DC Blocking Voltage	20	30	40	50	60	80	100	150	200	V
I _{F(AV)}	Maximum average forward Rectified Current	1.0									A
I _{FSM}	Non-repetitive peak forward surge current 8.3 ms singlehalf sine-wave	30									A
V _F	Maximum Forward Voltage at 1.0A DC	0.55			0.70		0.85		0.95		V
I _R	Maximum DC reverse current T _A =25°C at rated DC blocking voltage T _A =100°C	0.50					0.10				mA
		10					5.0				
C _J	Typical Junction Capacitance	110			90						pF
T _J	Operating Junction Temperature Range	-55 to +150									°C
T _{STG}	Storage Temperature Range	-55 to +150									°C
R _{θJA}	Thermal Resistance ⁽¹⁾	88									°C/W
R _{θJL}		28									

Note:(1) Thermal resistance from junction to ambient and from junction to lead mounted on P.C.B. with 0.2" x 0.2" (5.0 mm x 5.0 mm) copper pad areas



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Typical Performance Characteristics($T_J = 25^\circ\text{C}$, unless otherwise noted)

Figure 1: I_O - T_L Curve

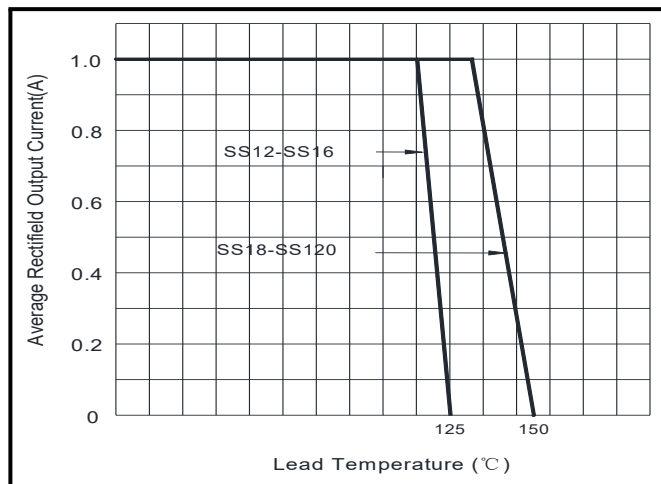


Figure 2: Surge Forward Current Capability

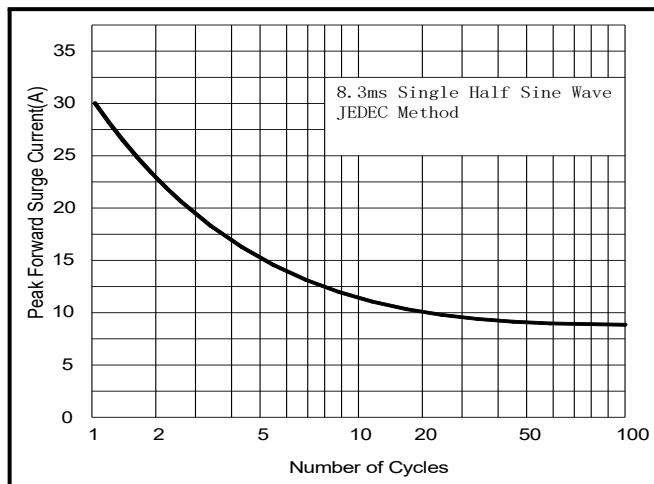


Figure 3: Typical Forward Characteristics

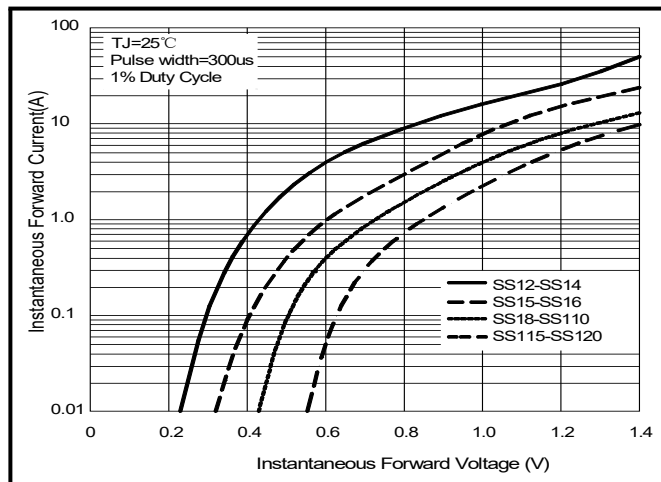
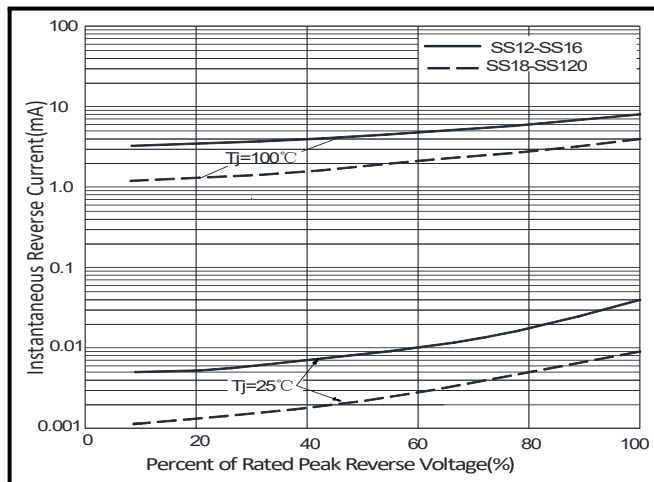


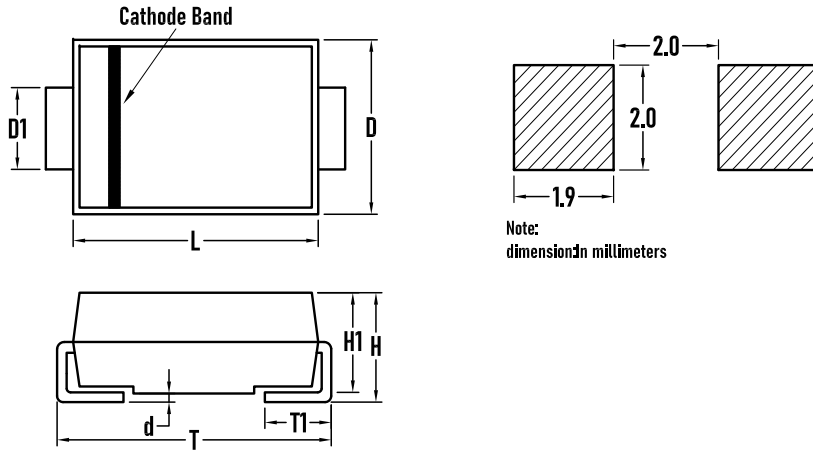
Figure 4: Typical Reverse Characteristics



SS12-SS120

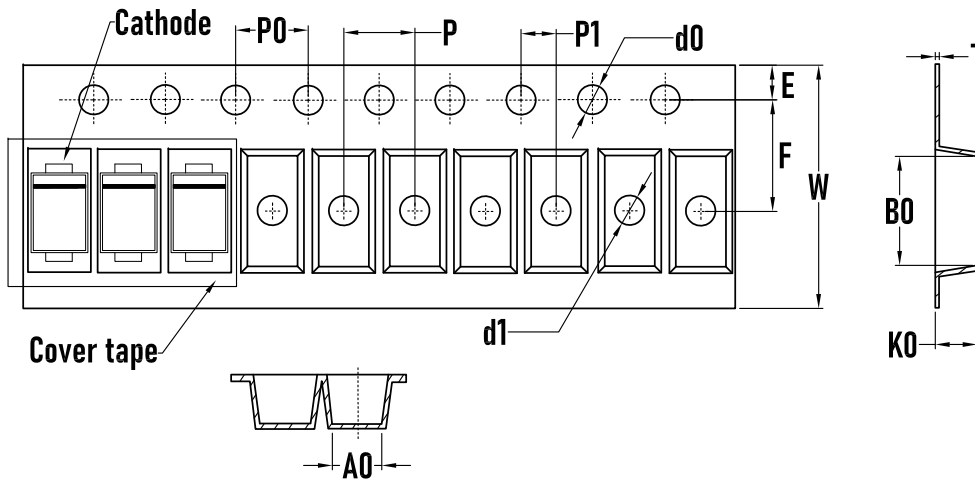
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Outline Drawing - SMA



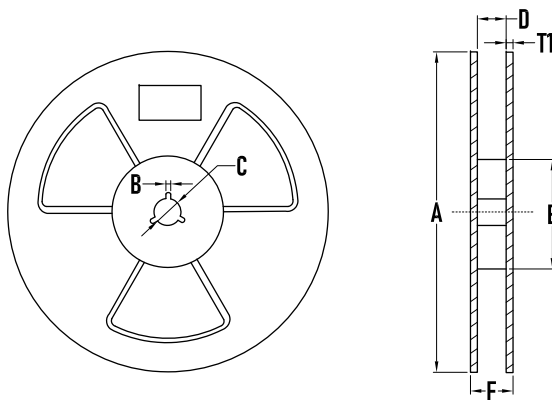
SYMBOL	MILLIMETER		Inches	
	MIN.	MAX.	MIN.	MAX.
D	2.5	2.9	0.098	0.114
D1	1.2	1.8	0.047	0.071
T	4.8	5.3	0.189	0.209
T1	0.8	1.5	0.031	0.059
d	—	0.2	—	0.008
H1	1.8	2.2	0.071	0.087
H	1.9	2.5	0.075	0.098
L	3.9	4.6	0.154	0.181

Packaging Tape - SMA



SYMBOL	MILLIMETER
A0	2.70
B0	5.10±0.1
d0	1.50±0.1
d1	1.50±0.1
E	1.75±0.1
F	5.50±0.1
K0	2.40±0.1
P	4.00±0.1
P0	4.00±0.1
P1	2.00±0.1
W	12.00±0.1
T	0.2±0.02

Packaging Reel



SYMBOL	MILLIMETER
A	323±2
B	3.0±0.2
C	15.0±0.5
D	13±2
E	73±2
T1	2.2±0.2
Quantity	5000PCS

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Specifications are subject to change without notice.

Please refer to <http://www.born-tw.com> for current information.

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